intersil

IRF9150

Data Sheet | February 1999 | File Number 2280.3

-25A, -100V, 0.150 Ohm, P-Channel Power MOSFET

This P-Channel enhancement mode silicon gate power field effect transistor is an advanced power MOSFET designed, tested, and guaranteed to withstand a specified level of energy in the breakdown avalanche mode of operation. All of these power MOSFETs are designed for applications such as switching regulators, switching convertors, motor drivers, relay drivers, and drivers for high power bipolar switching transistors requiring high speed and low gate drive power. These types can be operated directly from integrated circuits.

Formerly developmental type TA49230.

Ordering Information

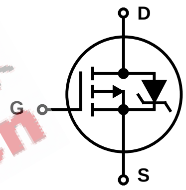
PART NUMBER	PACKAGE	BRAND
IRF9150	TO-204AE	IRF9150

NOTE: When ordering, use the entire part number.

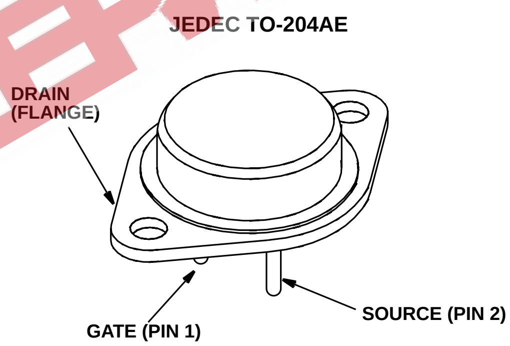
Features

- -25A, -100V
- $r_{DS(ON)} = 0.150\Omega$
- Single Pulse Avalanche Energy Rated
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance

Symbol



Packaging



Absolute Maximum Ratings $T_C = 25^oC$, Unless Otherwise Specified

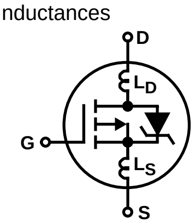
		IRF9150	UNITS
Drain to Source Breakdown Voltage (Note 1)	V_{DS}	-100	V
Drain to Gate Voltage ($R_{GS} = 20k\Omega$) (Note 1)	V_{DGR}	-100	V
Continuous Drain Current	I_D	-25	A
$T_C = 100^oC$	I_D	-18	A
Pulsed Drain Current (Note 3)	I_{DM}	-100	A
Gate to Source Voltage	V_{GS}	±20	V
Maximum Power Dissipation (Figure 1)	P_D	150	W
Linear Derating Factor		1.2	$W/^oC$
Single Pulse Avalanche Energy Rating (Note 4)	E_{AS}	1300	mJ
Avalanche Current (Repetitive or Nonrepetitive)	I_{AR}	-25	A
Operating and Storage Temperature	T_J, T_{STG}	-55 to 150	^oC
Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10s	T_L	300	^oC

CAUTION: Stresses above those listed in “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

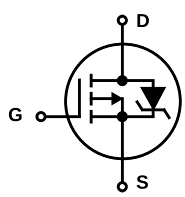
NOTE:

1. $T_J = 25^oC$ to $T_J = 125^oC$.

Electrical Specifications $T_C = 25^oC$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Drain to Source Breakdown Voltage	BV_{DSS}	$I_D = -250\mu A$, $V_{GS} = 0V$, (Figure 10)	-100	-	-	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = -250\mu A$	-2	-	-4	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = Rated BV_{DSS}, $V_{GS} = 0V$	-	-	-25	µA
		V_{DS} = 0.8 x Rated BV_{DSS}, $V_{GS} = 0V$ $T_C = 125^oC$	-	-	-250	µA
On-State Drain Current (Note 2)	$I_{D(ON)}$	$V_{DS} > I_{D(ON)} \times r_{DS(ON)MAX}$, $V_{GS} = 10V$	-25	-	-	A
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V$	-	-	±100	nA
Drain to Source On Resistance (Note 2)	$r_{DS(ON)}$	$I_D = -10A$, $V_{GS} = -10V$ (Figures 8, 9)	-	0.09	0.150	Ω
Forward Transconductance (Note 2)	g_{fs}	$V_{DS} = -10V$, $I_D = -12.5$ (Figure 12)	4	10	-	S
Turn-On Delay Time	$t_{d(ON)}$	$V_{DD} = -50V$, $I_D \approx -25A$, $R_G = 6.8\Omega$, $R_L = 2.0\Omega$, (Figures 17, 18) MOSFET Switching Times are Essentially Independent of Operating Temperature	-	16	24	ns
Rise Time	t_r		-	110	160	ns
Turn-Off Delay Time	$t_{d(OFF)}$		-	65	100	ns
Fall Time	t_f		-	46	70	ns
Total Gate Charge (Gate to Source + Gate to Drain)	$Q_{g(TOT)}$	$V_{GS} = -10V$, $I_D = -25A$, V_{DS} = 0.8 x Rated BV_{DSS} (Figures 14, 19, 20) Gate Charge is Essentially Indpendent of Operating Temperature	-	82	120	nC
Gate to Source Charge	Q_{gs}		-	14	-	nC
Gate to Drain “Miller” Charge	Q_{gd}		-	42	-	nC
Input Capacitance	C_{ISS}	$V_{DS} = -25V$, $V_{GS} = 0V$, f = 1MHz (Figure 11)	-	2400	-	pF
Output Capacitance	C_{OSS}		-	850	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	400	-	pF
Internal Drain Inductance	L_D	Measured Between the Contact Screw on the Flange that is Closer to Source and Gate Pins and the Center of Die Modified MOSFET Symbol Showing the Internal Devices Inductances 	-	5.0	-	nH
Internal Source Inductance	L_S	Measured From the Source Lead, 6mm (0.25in) From the Flange and the Source Bonding Pad	-	13	-	nH
Thermal Resistance Junction to Case	$R_{\theta JC}$		-	-	0.83	$^oC/W$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	Free Air Operation	-	-	30	$^oC/W$

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Continuous Source to Drain Current	I_{SD}	Modified MOSFET Symbol Showing the Integral Reverse P-N Junction Diode 	-	-	-25	A
Pulse Source to Drain Current (Note 3)	I_{SDM}		-	-	-100	A
Source to Drain Diode Voltage(Note 2)	V_{SD}	$T_C = 25^oC$, I_{SD} = 25A, V_{GS} = 0V (Figure 13)	-	0.9	1.5	V
Reverse Recovery Time	t_{rr}	$T_J = 25^oC$, I_{SD} = 25A, dI_{SD}/dt = 100A/µs	-	150	300	ns
Reverse Recovery Charge	Q_{RR}	$T_J = 25^oC$, I_{SD} = 25A, dI_{SD}/dt = 100A/µs	0.3	0.7	1.5	µC

NOTES:

2. Pulse test: pulse width ≤ 300µs, duty cycle ≤ 2%.
3. Repetitive rating: pulse width limited by maximum junction temperature. See Transient Thermal Impedance curve (Figure 3).
4. V_{DD} = 25V, starting $T_J = 25^oC$, L = 3.2mH, $R_G = 25\Omega$, peak I_{AS} = 25A See Figures 15, 16.

Typical Performance Curves Unless Otherwise Specified

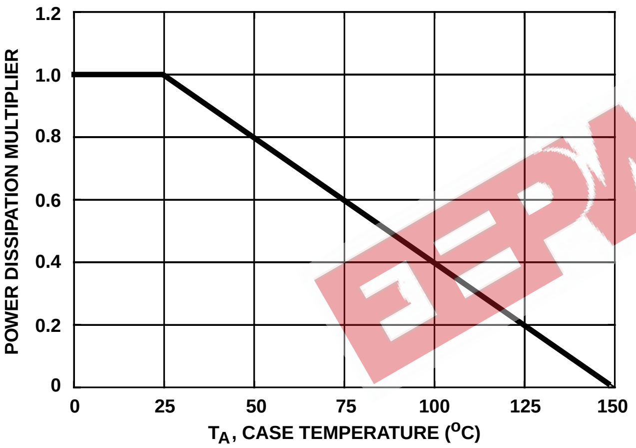


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

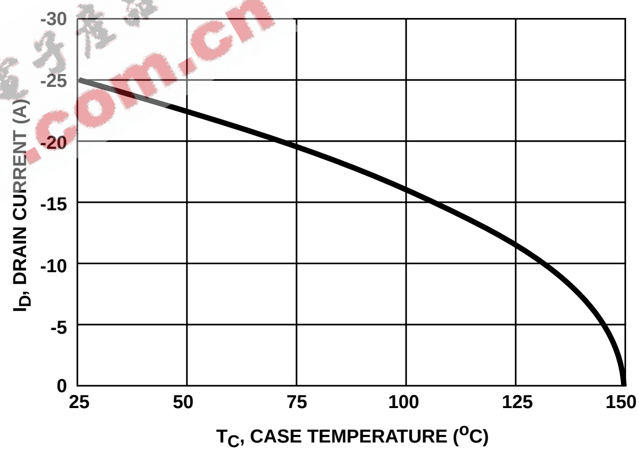


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

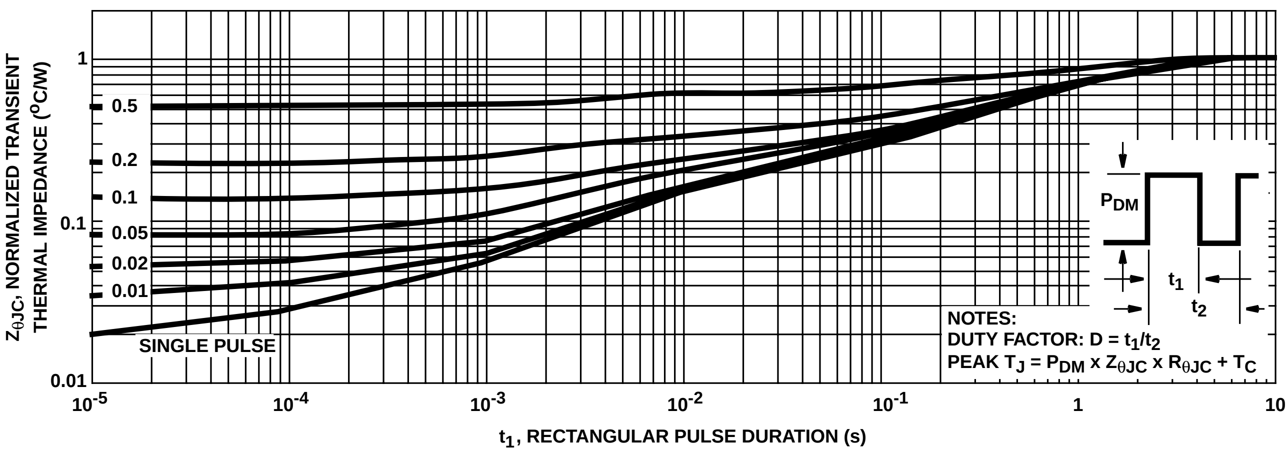


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

Typical Performance Curves Unless Otherwise Specified (Continued)

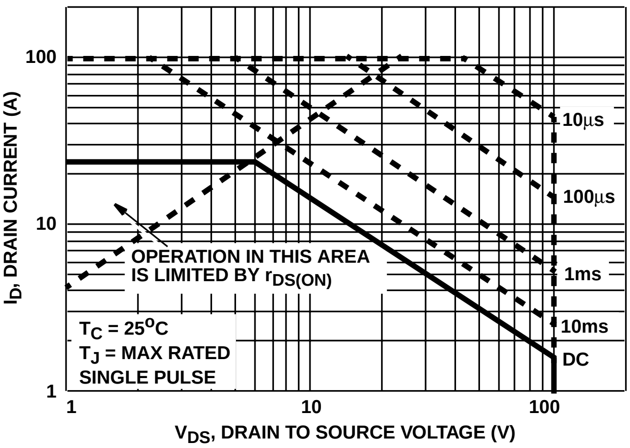


FIGURE 4. FORWARD BIAS SAFE OPERATING AREA

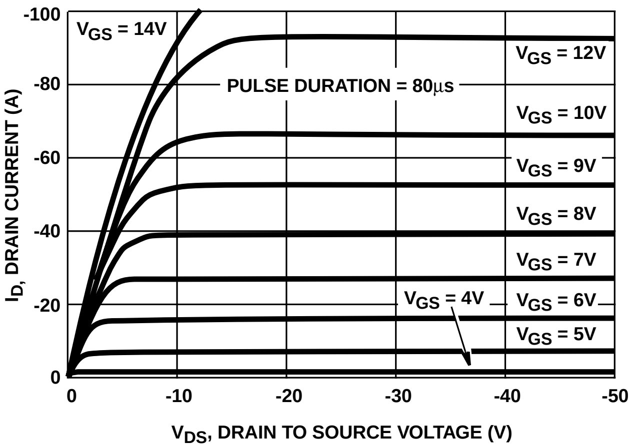


FIGURE 5. OUTPUT CHARACTERISTICS

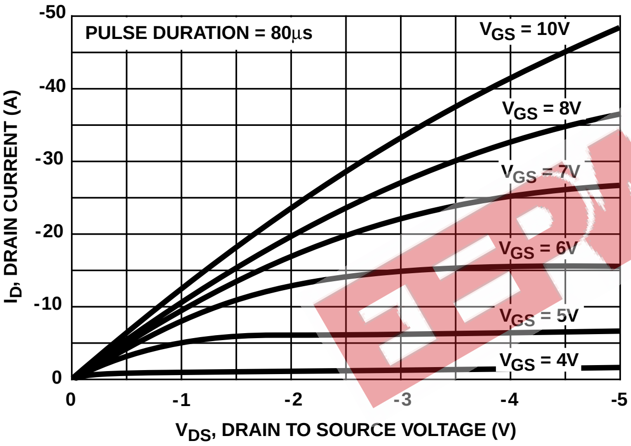


FIGURE 6. SATURATION CHARACTERISTICS

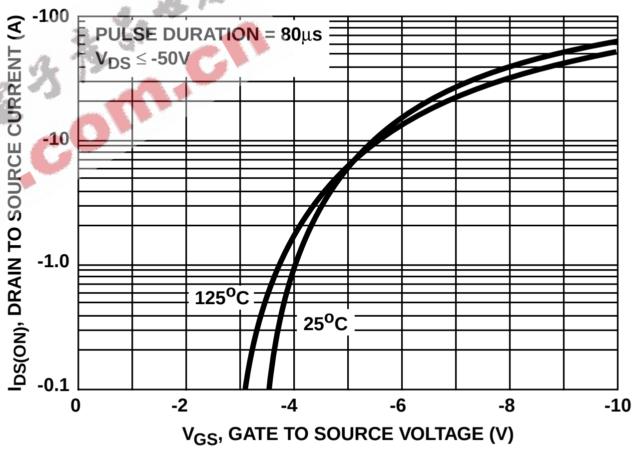


FIGURE 7. TRANSFER CHARACTERISTICS

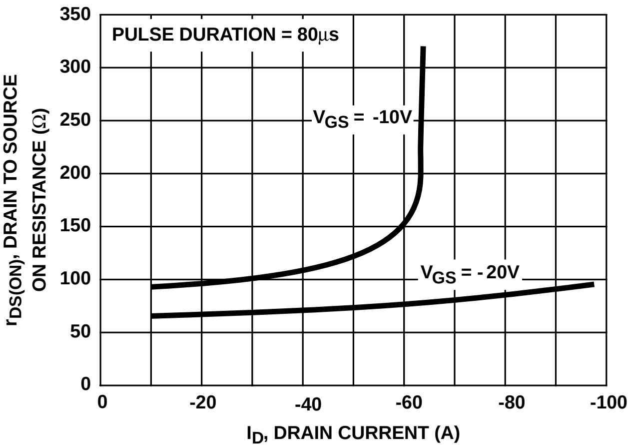


FIGURE 8. DRAIN TO SOURCE ON RESISTANCE vs GATE VOLTAGE AND DRAIN CURRENT

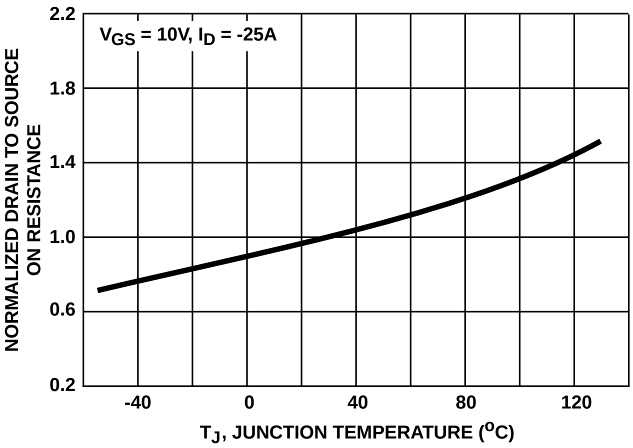


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

Typical Performance Curves Unless Otherwise Specified **(Continued)**

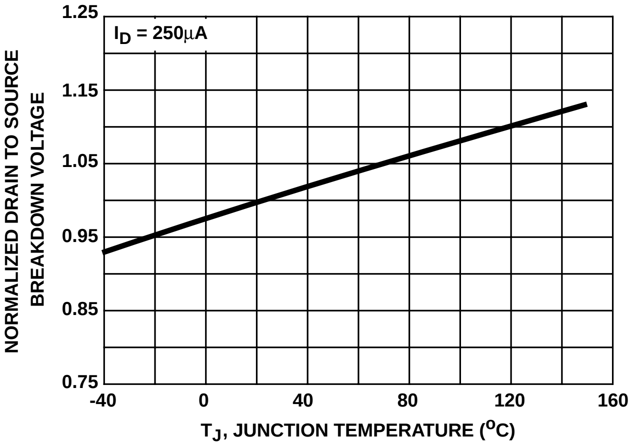


FIGURE 10. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

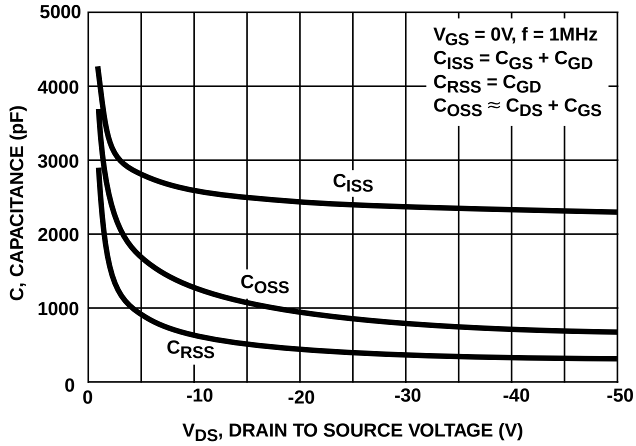


FIGURE 11. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE

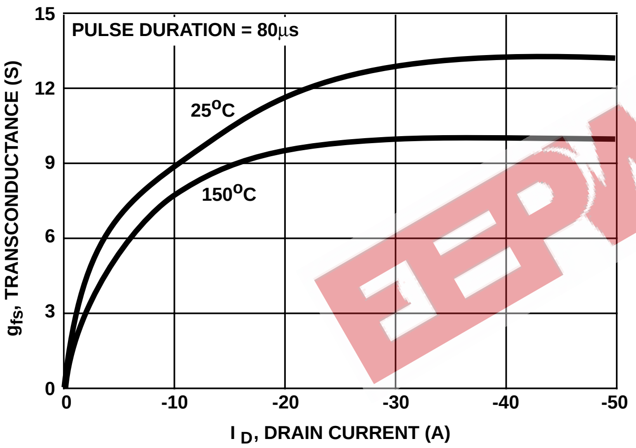


FIGURE 12. TRANSCONDUCTANCE vs DRAIN CURRENT

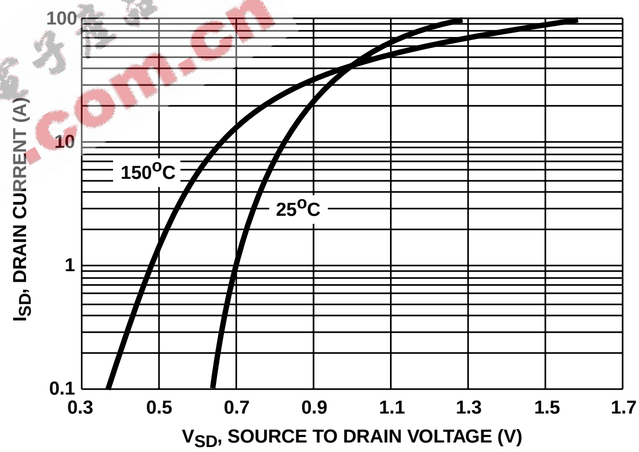


FIGURE 13. SOURCE TO DRAIN DIODE VOLTAGE

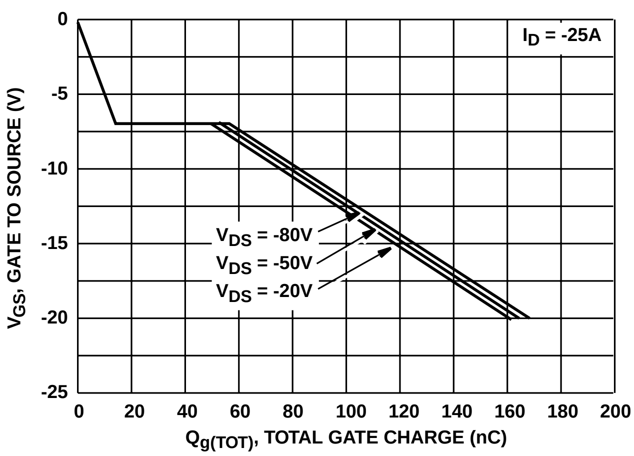


FIGURE 14. GATE TO SOURCE VOLTAGE vs GATE CHARGE

Test Circuits and Waveforms

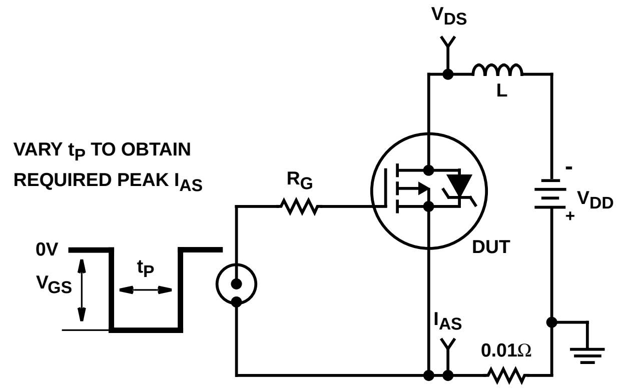


FIGURE 15. UNCLAMPED ENERGY TEST CIRCUIT

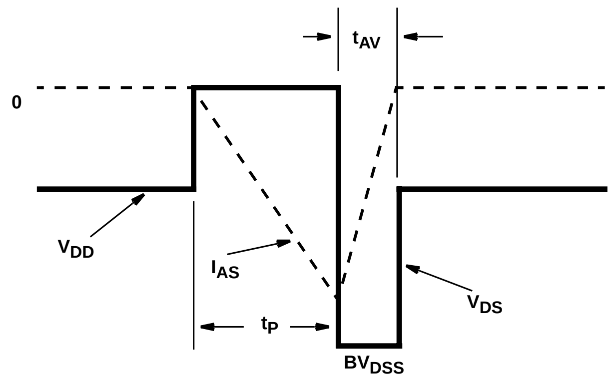


FIGURE 16. UNCLAMPED ENERGY WAVEFORMS

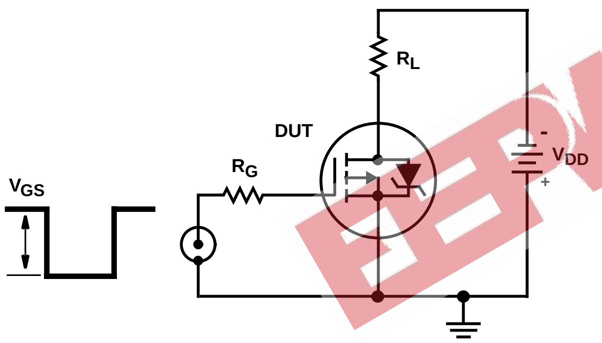


FIGURE 17. SWITCHING TIME TEST CIRCUIT

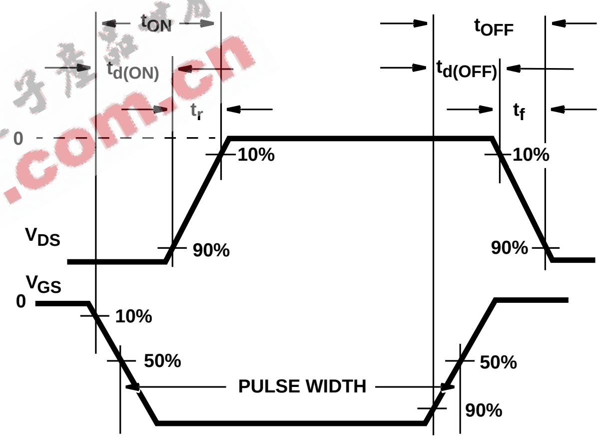


FIGURE 18. RESISTIVE SWITCHING WAVEFORMS

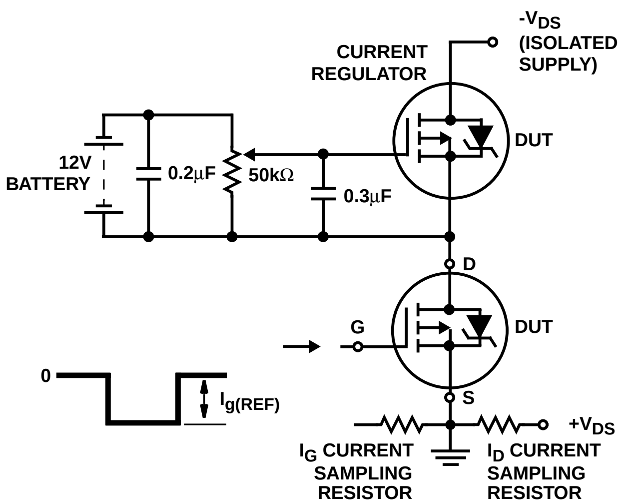


FIGURE 19. GATE CHARGE TEST CIRCUIT

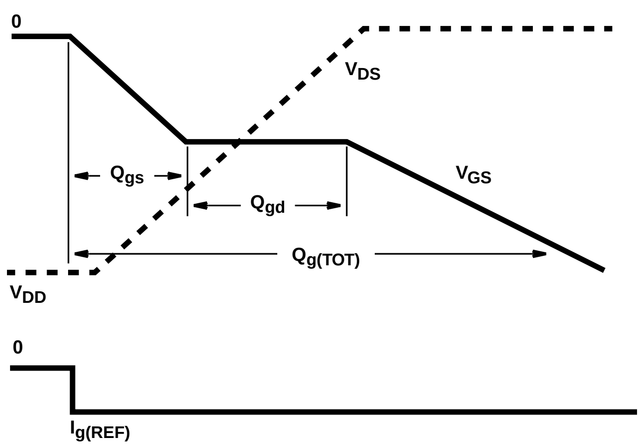


FIGURE 20. GATE CHARGE WAVEFORMS

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